MP5512

18V, 4.5A, High-Efficiency Energy Storage and Management Unit for SSD Applications

The Future of Analog IC Technology

DESCRIPTION

MP5512 is a high-efficiency energy storage and management unit targeting solid-state and hard-disk drive applications. Its highly integrated input-current limit and energy storage and release management provide an efficient, compact system solution for SSD applications.

The internal input-current-limit block with dv/dt control prevents an inrush current during system start-up. The bus voltage start-up slew rate is programmable; it includes a power-on-reset function for hot-swapping. MPS' patented energy-storage and release-management control circuit minimizes the storage capacitor requirement. It boosts the input voltage to a higher storage voltage and releases the energy over a hold-up time in case of an input outage. The storage voltage and the release voltage are both programmable for different system applications.

The MP5512 requires a minimal number of standard, external components and is available in a 28-pin QFN (4mm×5mm) package.

FEATURES

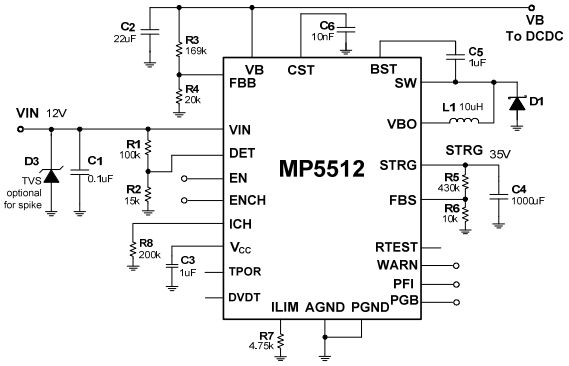
- Wide 4V-to-18V Operating Input Range
- Programmable Storage Voltage Up to 40V
- Programmable Input-Current Limit Up to 4.5A
- Input Reverse-Current Protection
- Adjustable dv/dt Slew Rate for Bus Voltage Start-up
- 14mΩ MOSFET for Input Hot-swap
- Internal 140mΩ and 110mΩ Power Switches for Energy-Storage and Release-Management Circuits
- V_B Power-Good Indicator
- Input-Failure Indicator and Input-Early Warning for V_{IN} Voltage
- ±3% Input-Current Limit at 2A
- 0.1uF Input capacitor for Hot-swap
- Thermal Protection
- Available in a QFN28 (4mm×5mm) Package

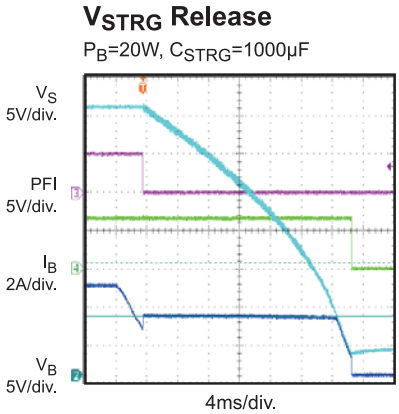
APPLICATIONS

- Solid-State Drives
- Hard-Disk Drives
- Power Back-up Systems

All MPS parts are lead-free, halogen free, and adhere to the RoHS directive. For MPS green status, please visit MPS website under Quality Assurance.
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TYPICAL APPLICATION





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ORDERING INFORMATION

Part Number*	Package	Top Marking
MP5512GV	QFN-28 (4mmx5mm)	*See Below*

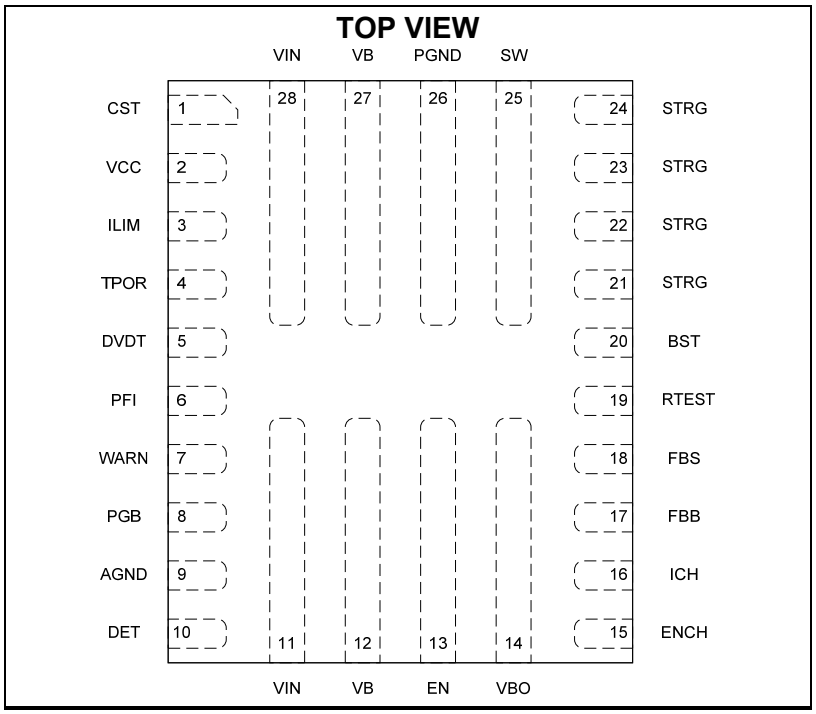
* For Tape & Reel, add suffix –Z (e.g. MP5512GV–Z);

TOP MARKING

MPSYWW
MP5512
LLLLLL

MPS: MPS prefix;
Y: year code;
WW: week code:
MP5512: product code of MP5512GV;
LLLLLL: lot number;

PACKAGE REFERENCE



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ABSOLUTE MAXIMUM RATINGS (1)

Supply Voltage V_{IN} .....-0.3V to 20V
VB, VBO .....-0.3V to 20V
V_{STRG}, V_{RTEST} .....-0.3V to 50V
V_{SW}.....-0.3V(-4V for <5ns) to V_{STRG}+0.3V
V_{BST} .....-0.3V to V_{STRG}+6.5V
V_{CST} .....-0.3V to 28V
All Other Pins.....–0.3V to 6.5 V
EN, ENCH Current..... 0.3mA(2)
Continuos Power Dissipation (T_A = +25°C) (3)
..... 3.28W
Junction Temperature.....150°C
Lead Temperature .....260°C
Storage Temperature..... –65°C to +150°C

Recommended Operating Conditions (4)

Supply Voltage V_{IN} .....4V to 18V
Bus Voltage V_B.....4V to 18V
Storage Voltage V_{STRG} .....V_{IN_MAX}+3V to 40V
Max. Input Current 4.5A
Max. Buck-Release Current..... 3A
EN, ENCH Current..... 0mA to 0.2mA(2)
Operating Junction Temp. (T_J). -40°C to +125°C

Thermal Resistance (5)	θ_{JA}	θ_{JC}	
QFN-28 (4mmx5mm) ……. …..38	38	8	°C/W

Notes:

1) Exceeding these ratings may damage the device.
2) Refer to the “Enable Control” section.
3) The maximum allowable power dissipation is a function of the maximum junction temperature T_J (MAX), the junction-to-ambient thermal resistance θ_{JA}, and the ambient temperature T_A. The maximum allowable continuous power dissipation at any ambient temperature is calculated by P_D (MAX) = (T_J (MAX)-T_A)/θ_{JA}. Exceeding the maximum allowable power dissipation will cause excessive die temperature, and the regulator will go into thermal shutdown. Internal thermal shutdown circuitry protects the device from permanent damage.
4) The device is not guaranteed to function outside of its operating conditions.
5) Measured on JESD51-7, 4-layer PCB.

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ELECTRICAL CHARACTERISTICS

V_{IN} = 12V, V_{EN} = V_{ENCH} = 2V, T_J = -40°C to 125°C, typical value is tested at T_J = 25°C, unless otherwise noted.

Parameter	Symbol	Condition	Min	Typ	Max	Units
Input-Supply Voltage Range	V_{IN}		4		18	V
Supply Current (Shutdown)	I_S	V_{EN}=0V, T_J = 25°C		3	5	μA
Supply Current (Quiescent)	I_Q	$V_{EN/ENCH}$=2V, $V_{FBB/FBS/DET}$=1V		1	2	mA
V_{CC} Regulator	V_{CC}	Vin or VB=6V, Ivcc=1mA	4.8	5.1	5.5	V
VIN Under-Voltage Lockout Threshold Rising	$INUV_R$		2.5	2.9	3.2	V
VIN Under-Voltage Lockout Threshold Hysteresis	$INUV_{HYS}$			0.35		V
EN UVLO Threshold Rising	EN_R				1.2	V
EN UVLO Threshold Falling	EN_F		0.4			V
V_{IN} to V_B Current Limit FET ON Resistance	R_{DSON}			14		mΩ
Continuous-Current Limit	I_{LIM}	R_{ILIM}=8.25kΩ, T_J = 25°C	1.94	2	2.06	A
		R_{ILIM}=8.25kΩ， T_J = -40°C to 125°C	1.9	2	2.1	A
Current Monitor Output	V_{ILIM}	R_{ILIM}=8.25kΩ, I_B=2A, T_J = 25°C	1.152	1.2	1.248	V
Off-State Leakage Current	I_{LEAK}	V_{IN}=12V, V_B=0V or V_B=12V, V_{IN}=0V, T_J = 25°C		2	4	μA
VB Rise Time (dv/dt) Control[6]	τ_R	DVDT floating, V_{IN}=12V, test VB rise time		0.9		ms
	I_{DVDT}	Connect capacitor to DVDT, test DVDT charge current		1		μA
Internal RESET Delay-Time Control [6]	τ_D	TPOR floating, test reset delay time		0.35		ms
	I_{TPOR}	Connect capacitor to TPOR, test TPOR charge current		1		μA
Pre-Charge Current	I_{CH_PRE}			450		mA
Charge Peak Current @ Boost Mode	I_{CH}	ICH floating, L=10μH, T_J = 25°C	670	960	1250	mA
Boost-Disconnect Switch R_{on}	R_{dison}			30		mΩ
Energy Management HS R_{on}	R_{Hon}			140		mΩ
Energy Management LS R_{on}	R_{Lon}			110		mΩ
Feedback Voltage	$V_{FBB-REF}$, $V_{FBS-REF}$, $V_{DET-REF}$	T_J = 25°C	0.792	0.8	0.808	V
		T_J = -40°C to 125°C	0.784	0.8	0.816	V
Feedback Current	I_{FBB}, I_{FBS}, I_{DET}	V_{FBB}=V_{FBS}=V_{DET}=0.8V		10	50	nA
Vs Over-Voltage Threshold	V_{S-OVP}			1.1		$V_{FBS-REF}$

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ELECTRICAL CHARACTERISTICS *(continued)*

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Parameter	Symbol	Condition	Min	Typ	Max	Units
STRG Pin Leakage Current		EN=2V, ENCH=0V, STRG=40V, T_J=25°C		60	100	μA
V_{IN} to V_B Current Limit FET Turn-On Voltage	$V_{IN-VB-ON}$	T_J = 25°C	130	190	250	mV
V_{IN} to V_B Current Limit FET Shut-Down Current	$I_{IN-VB-OFF}$	T_J = 25°C	-350	-150	-30	mA
$WARN_{IN}$ High Threshold	$WARN_{H_IN}$			1.08		$V_{DET-REF}$
$WARN_{IN}$ Low Threshold	$WARN_{L_IN}$			1.06		$V_{DET-REF}$
$WARN_{IN}$ Delay	$WARN_{D_IN}$			5		μs
$WARN_{IN}$ Sink-Current Capability	V_{WARN_IN}	Sink 2mA			0.3	V
$WARN_{IN}$ Leakage Current	I_{WARNIN_L}	V_{WARN}=5V		10		nA
PFI High Threshold	PFI_H			1.02		$V_{DET-REF}$
PFI Low Threshold	PFI_L			0.99		$V_{DET-REF}$
PFI Delay	PFI_{D_F}	PFI falling		2.4		μs
	PFI_{D_R}	PFI rising		1.3		ms
PFI Sink-Current Capability	V_{PFI}	Sink 2mA			0.3	V
PFI Leakage Current	I_{PFI}	V_{PFI}=5V		10		nA
PG_B High Threshold	PG_{H_VB}			0.95		$V_{FBB-REF}$
PG_B Low Threshold	PG_{L_VB}			0.9		$V_{FBB-REF}$
PG_B Delay	PG_{D_VB}			5		μs
PG_B Sink-Current Capability	V_{PG_VB}	Sink 2mA			0.3	V
PG_B Leakage Current	I_{PGB_L}	V_{PGIN}=5V		10		nA
Buck-Mode Dumping-Peak-Current Limit	$I_{DUMP-PEAK}$			5		A
Buck-Mode Dumping-Valley-Current Limit	$I_{DUMP-VALLEY}$			2.8		A
Release-Buck Switching Frequency	f_{s_RLS}	V_{STRG} from 40V to 12V		500		kHz
VB Under-Voltage Lockout Threshold, Rising(7)	$INUVB_R$		2.3	2.6	2.8	V
VB Under-Voltage Lockout Threshold, Hysteresis(7)	$INUVB_{HYS}$			0.2		V
Thermal Shutdown(8)	T_{SD}			150		°C
Thermal Shutdown Hysteresis(8)	T_{HYS}			30		°C

Notes:

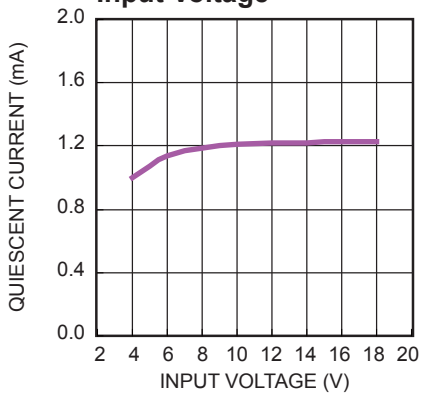
6) Refer to “Power-on Reset Delay and VB Rising Control” section for detail calculation.
7) VB UVLO is applied to Energy Storage and Release Circuitry.
8) Guaranteed by characterization, not production tested.

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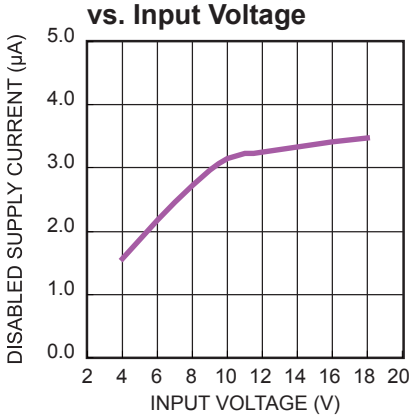
TYPICAL CHARACTERISTICS

V_{IN} = 12V, V_{STRG} = 35V, V_{PFI} = 6.1V, V_{RLS} = 7.8V[9], L = 10µH, P_{OUT} = 20W, T_A = 25ºC, unless otherwise noted.

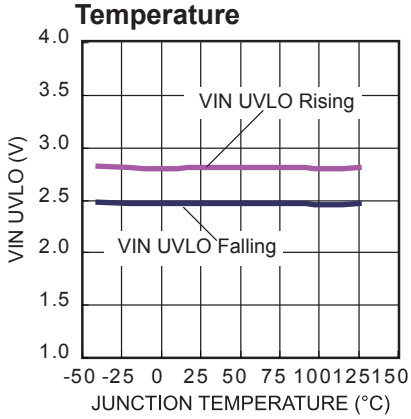
Quiescent Current vs. Input Voltage



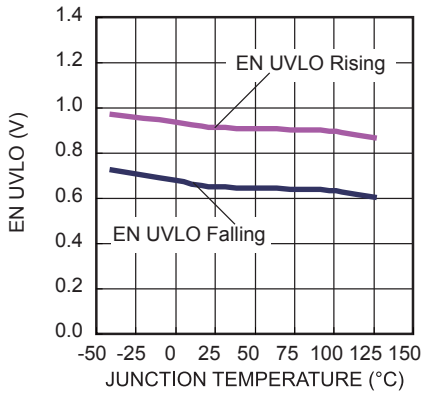
Disabled Supply Current vs. Input Voltage



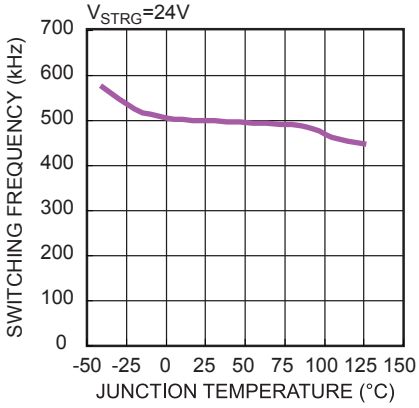
Vin UVLO Threshold vs. Temperature



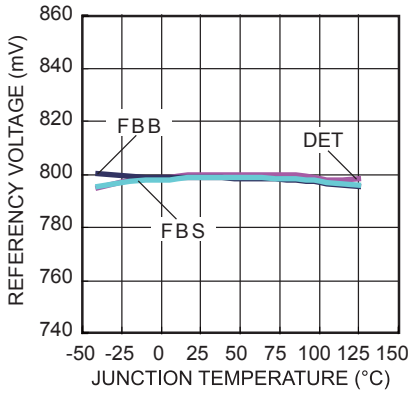
EN UVLO Threshold vs. Temperature



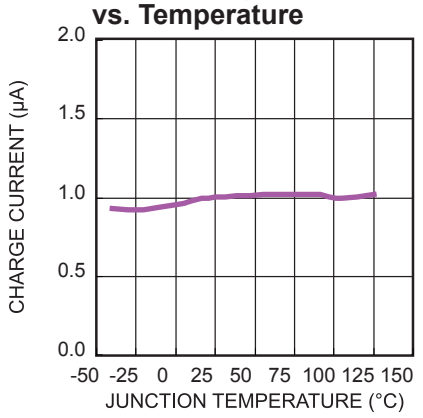
Switching Frequency vs. Temperature



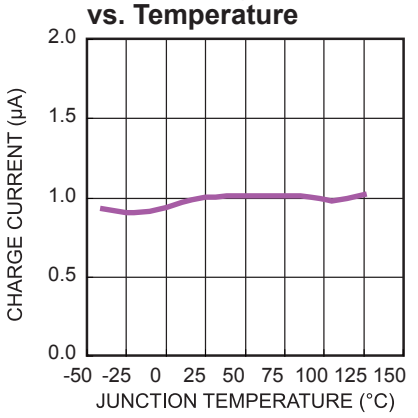
Reference Voltage vs. Temperature



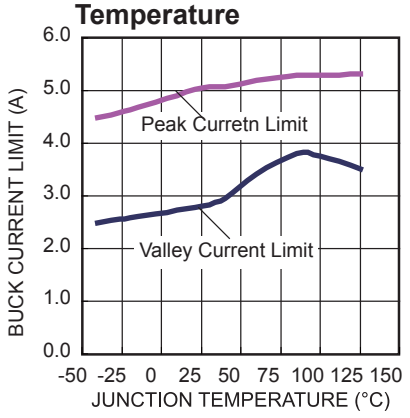
DVDT Charge Current vs. Temperature



TPOR Charge Current vs. Temperature



Buck-Current Limit vs. Temperature

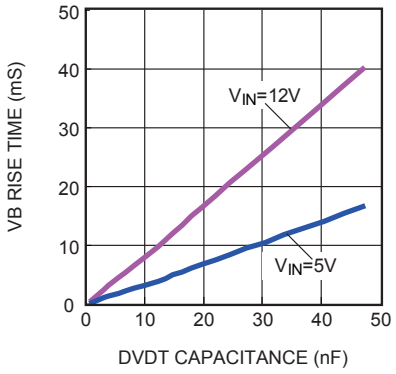


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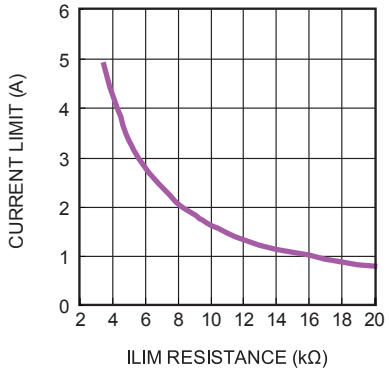
TYPICAL CHARACTERISTICS *(continued)*

V_{IN} = 12V, V_{STRG} = 35V, V_{PFI} = 6.1V, V_{RLS} = 7.8V(9), L = 10µH, P_{OUT} = 20W, T_A = 25ºC, unless otherwise noted.

VB Rising Time vs. DVDT Capacitance

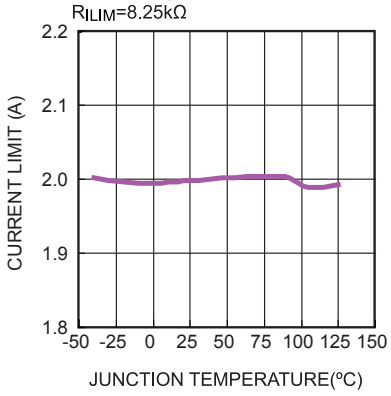


VIN to VB Current Limit vs. ILIM Resistor



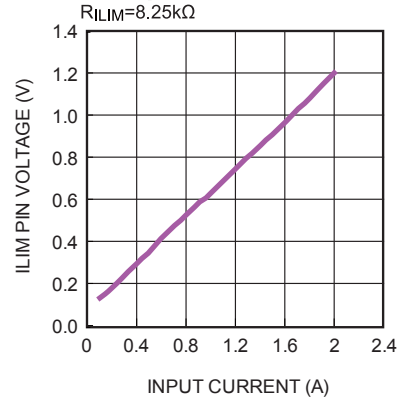
VIN to VB Current Limit vs. Temperature

R_{ILIM}=8.25kΩ

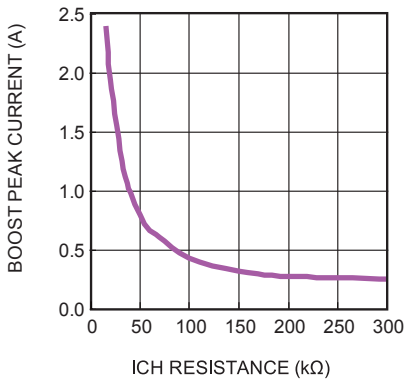


ILIM Monitor Voltage vs. Input Current

R_{ILIM}=8.25kΩ

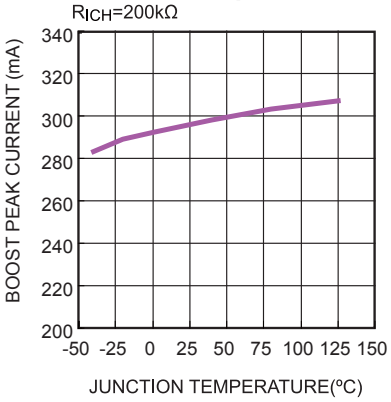


Boost-Charge Peak Current vs. ICH Resistor

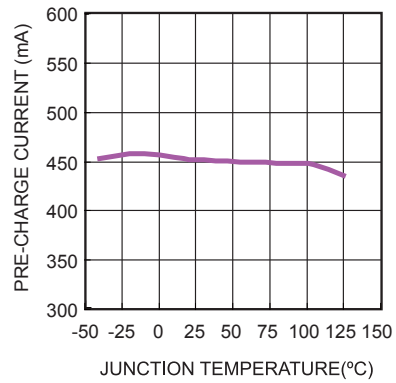


Boost-Charge Peak Current Limit vs. Temperature

R_{ICH}=200kΩ



Boost Pre-charge Current vs. Temperature



Notes:

9) V_{RLS} voltage varies a little with different V_{STRG} voltage because the internal RAMP voltage on FBB changes with duty cycle. 7.8V voltage is estimated based on 30V V_{STRG} condition.

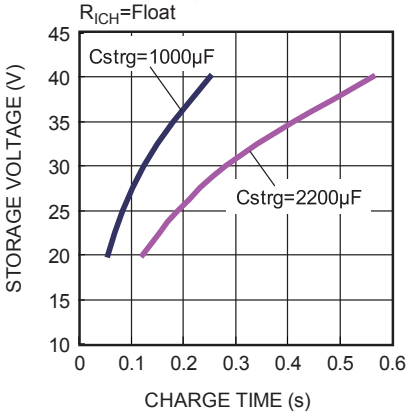
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TYPICAL PERFORMANCE CHARACTERISTICS

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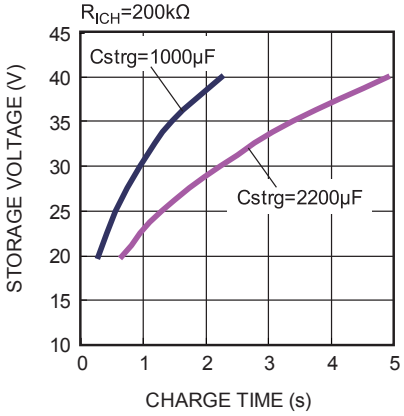
Storage-Charge Voltage vs. Charge Time

R_{ICH}=Float

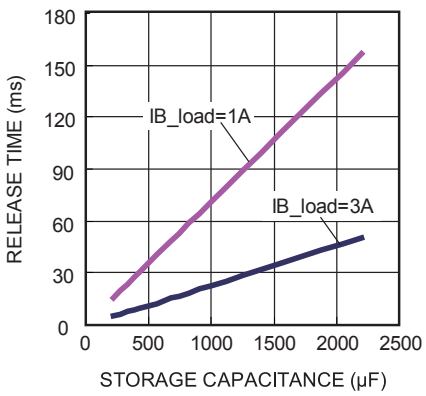


Storage-Charge Voltage vs. Charge Time

R_{ICH}=200kΩ

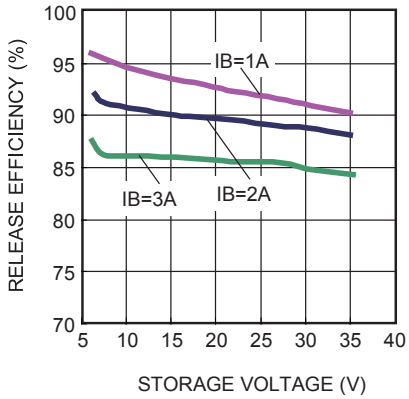


Release Time vs. Storage Capacitance



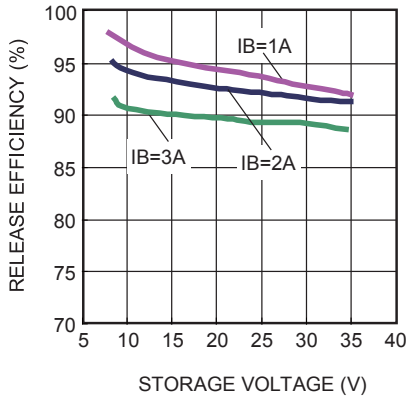
Backup-Release Efficiency

VB_RLS=5V



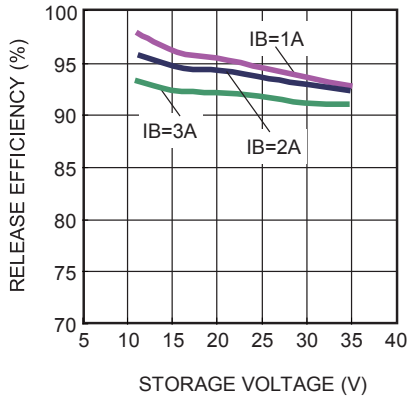
Backup-Release Efficiency

VB_RLS=7.8V



Backup-Release Efficiency

VB_RLS=10V

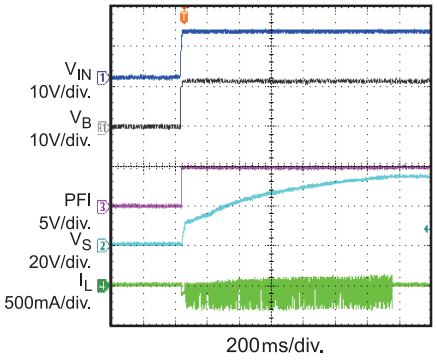


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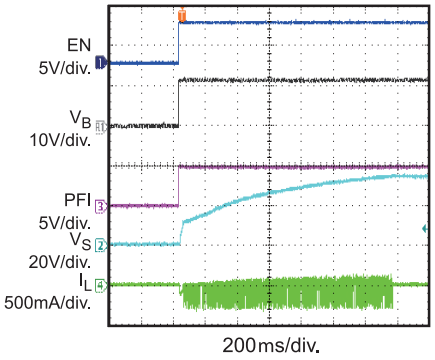
TYPICAL PERFORMANCE CHARACTERISTICS *(continued)*

V_{IN} = 12V, V_{STRG} = 35V, V_{PFI} = 6.1V, V_{RLS} = 7.8V[9], L = 10µH, T_A = 25ºC, P_{OUT} = 20W, unless otherwise noted.

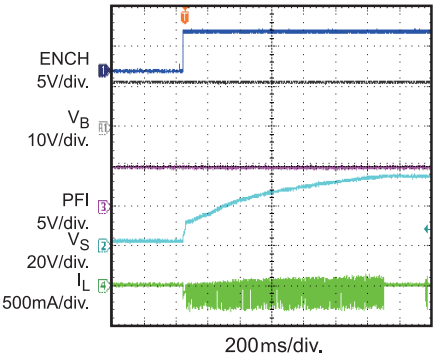
V_{IN} Power On



EN Power On

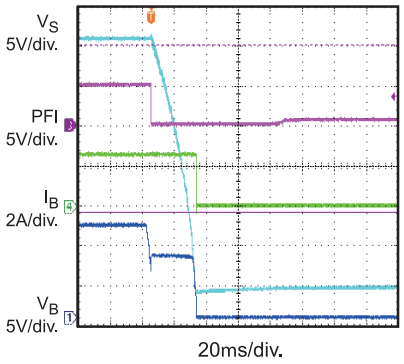


ENCH Power On



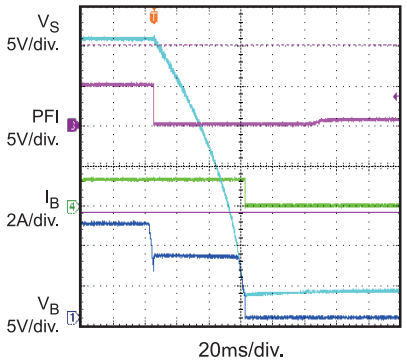
V_{STRG} Release

P_B=20W, C_{STRG}=1000µF



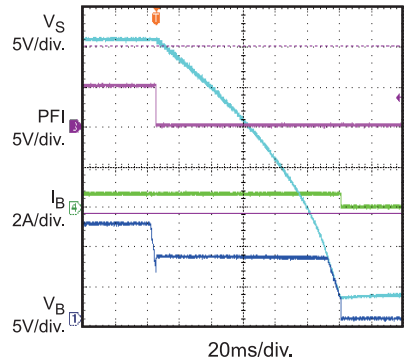
V_{STRG} Release

P_B=10W, C_{STRG}=1000µF



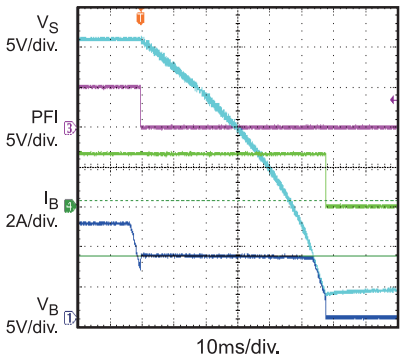
V_{STRG} Release

P_B=5W, C_{STRG}=1000µF



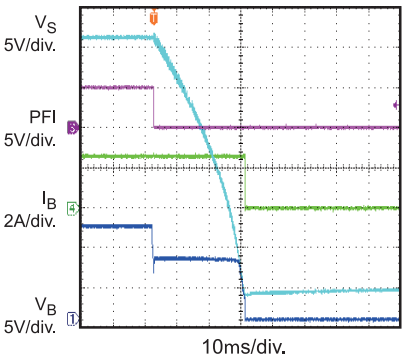
V_{STRG} Release

P_B=20W, C_{STRG}=2200µF



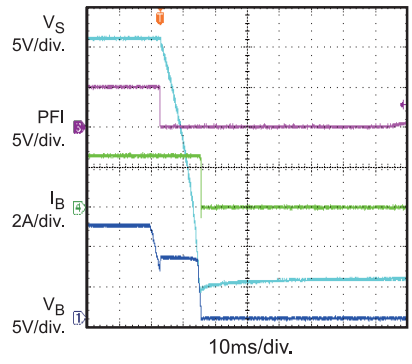
V_{STRG} Release

P_B=20W, C_{STRG}=1000µF



V_{STRG} Release

P_B=20W, C_{STRG}=440µF



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PIN FUNCTIONS

QFN28 (4mm×5mm) Pin #	Name	Description
1	CST	Storage Capacitor for Internal Charge Pump. Requires 10nF decouple capacitor between CST and AGND to drive the MOSFET current limit. Do not connect to a capacitor with over 47nF.
2	VCC	Internal LDO Output. VCC provides power for internal circuits. Decouple with a 1μF ceramic capacitor. Connect the capacitor as close to VCC as possible.
3	ILIM	DC Input Current Limit. Connect a resistor between ILIM and AGND to adjust the DC limit from VIN to VB.
4	TPOR	Power-On-Reset Delay. Connect a capacitor between TPOR and AGND to determine the power-on-reset delay time. During the default power-on-reset delay time, leave TPOR floating for 0.35ms.
5	DVDT	Bus Voltage Start-Up Slew Rate. Connect a capacitor from DVDT to AGND. Leave it floating for the default soft-start time (around 0.9ms from 0V to 12V).
6	PFI	Power-Failure Indicator. PFI is an open-drain output. To indicate a signal, PFI should be pulled up to a power source through a resistor. PFI goes high if the DET voltage exceeds $1.02\times V_{DET-REF}$. PFI goes low if the DET voltage drops below $0.99\times V_{DET-REF}$. If MP5512 is disabled by UVLO or EN UVLO, it operates with high impedance.
7	WARN	VIN Voltage-Drop Warning Indicator. WARN is an open-drain output. To indicate a signal, WARN should be pulled up to a power source through a resistor. WARN goes high if the DET voltage exceeds $1.08\times V_{DET-REF}$. WARN goes low if the DET voltage drops below $1.06\times V_{DET-REF}$. WARN indicates the input power distance to the set supply-voltage level. If MP5512 is disabled by UVLO or EN UVLO, it operates with high impedance.
8	PGB	Bus Voltage Power-Good Indicator. PGB is an open-drain output. To indicate a signal, PGB should be pulled up to a power source through a resistor. PGB goes high if the FBB voltage exceeds $0.95\times V_{FBB-REF}$. PGB goes low if the FBB voltage drops below $0.9\times V_{FBB-REF}$. If MP5512 is disabled by UVLO or EN UVLO, it operates with high impedance.
9	AGND	IC Signal Ground.
10	DET	Input-Voltage Detection Sense. DET sets the buck-release start voltage when V_{IN} drops.
11, 28	VIN	Input-Supply Voltage. The MP5512 operates from an unregulated 4V-to-18V input. Place a 0.1μF ceramic capacitor as close to VIN as possible. A TVS diode at input is necessary if the V_{IN} voltage spike is high. Refer to the “Selecting Input Capacitor and TVS” sections.
12, 27	VB	Bus Voltage. VB requires a 22μF-to-47μF ceramic capacitor as close to VB as possible.
13	EN	ON/OFF Control. EN enables/disables all internal circuits.
14	VBO	Source of Internal Isolation MOSFET. Connect the inductor between SW and VBO for boost and buck operation.
15	ENCH	Boost Converter ON/OFF Control. ENCH enables/disables the energy-storage function but does not limit the release function.
16	ICH	Boost-Mode Charge Switching-Peak Current Adjustment.

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PIN FUNCTIONS *(continued)*

QFN28 (4mm×5mm) Pin #	Name	Description
17	FBB	Bus-Voltage Feedback Sense. FBB Regulates the bus voltage in buck mode.
18	FBS	Storage-Voltage Feedback Sense. FBS sets the storage voltage in boost mode.
19	RTEST	STRG residual energy discharge resistor connection pin in evaluation test. When Vin/VB or EN powers off, RTEST is pulled to PGND internally. One external resistor from RTEST to STRG discharges STRG voltage for a residual energy discharge. The discharge current must be lower than 500mA. This discharge resistor can avoid any spark if we touch STRG after IC disabled in evaluation test.
20	BST	Bootstrap. Requires the bootstrap capacitor from BST to SW to supply the high-side switch driver.
21,22,23,24	STRG	Storage. Connect the storage capacitor for energy storage and release circuitry.
25	SW	Switch output. For energy storage and release circuitry, connect a small inductor between SW and VBO.
26	PGND	Power Ground.

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FUNCTION DIAGRAM

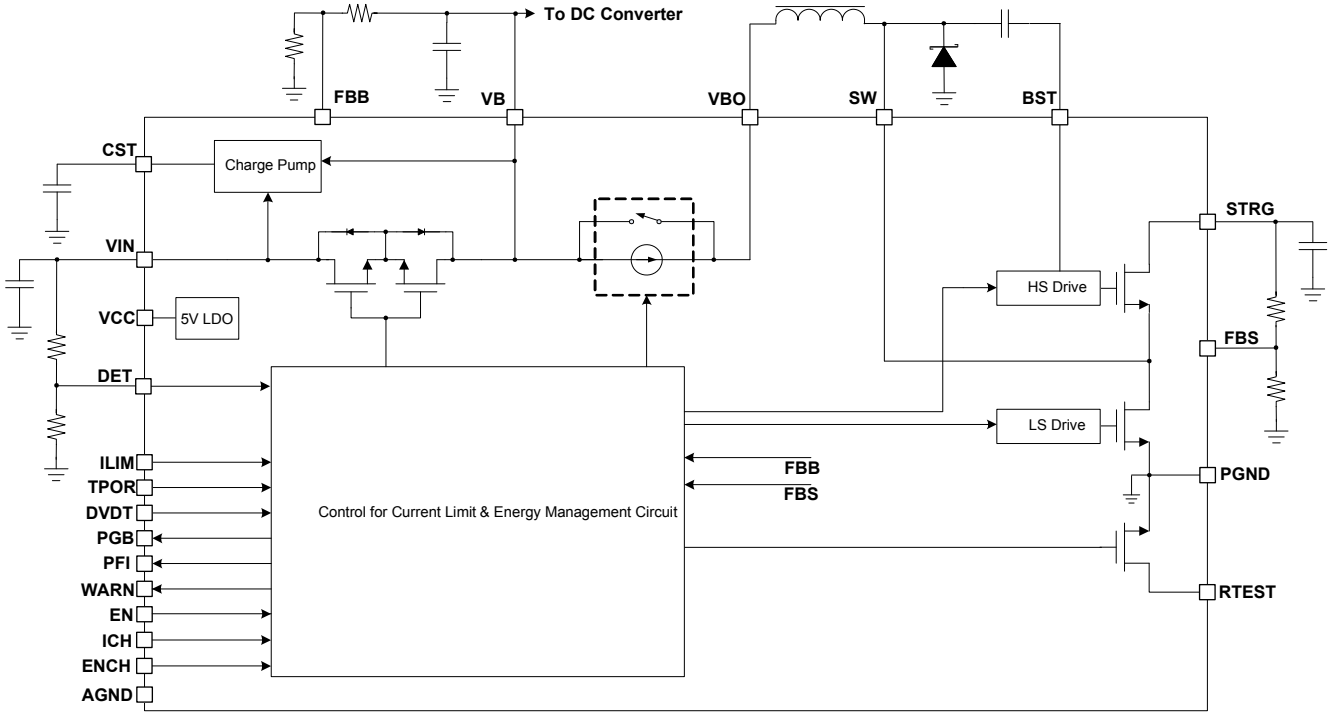


Figure 1: Functional Block Diagram

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OPERATION

The MP5512 is an energy storage and management unit in a 4mm×5mm 28-pin QFN package. It provides a compact and efficient energy management solution for typical solid-state–drive or hard-disk drive applications. MPS' patented lossless-energy storage and release-management circuits use a bi-directional buck/boost converter to achieve optimal energy transfer and provide a cost-effective energy-storage solution.

MP5512's built-in boost-mode converter charges the storage bulk capacitor to a programmed voltage when the system is powered up. In case of an input power failure, MP5512 flags the power failure, disconnects the input power and transfers the energy from the storage capacitor to the bus capacitor via the built-in buck mode converter. This supports SSD system data backup. The buck converter works in 100% duty-cycle operation to fully deplete the stored energy.

Start-Up

When the VIN power and enable signal are higher than their UVLO, MP5512 starts up with the programmed power-on-reset delay time. Initially, the hot-swap MOSFET from VIN to VB is on and the bus capacitor is charged from 0 to V_{IN} under dv/dt control.

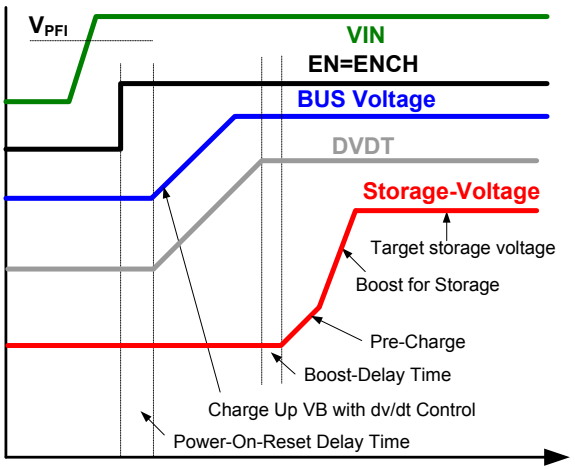


Figure 2: Charging Process

When DET voltage is higher than 1.02×$V_{DET-REF}$, PFI is set to high to indicate the power condition. If PFI is high and dv/dt voltage is saturated, the charge circuit is enabled to charge storage capacitors on STRG (after about 1.8ms delay time). The storage voltage is charged with 450mA trickle current during the pre-charge period. Once the storage voltage is close to VB voltage, the boost-switching circuit initiates and the storage voltage is boosted to the target voltage (see Figure 2).

Storage Voltage

After the start-up period, the internal boost converter automatically regulates the storage voltage to the set value. The MP5512 uses burst mode to minimize the converter's power loss. When the storage voltage drops below the set voltage, burst mode initiates and charges the storage capacitor. During the burst period, the current limit and the low-side MOSFET control the boost. When the power MOSFET turns on, the inductor current increases until it reaches its current limit. After hitting the current limit, the power MOSFET turns off for the set minimum off time. If the feedback voltage remains below the 0.8V internal reference at the end of the minimum off time, the power MOSFET turns on again. Otherwise, the MP5512 waits until the voltage drops below the reference threshold before turning on. In boost mode, the high-side MOSFET won't turn on and the inductor current conducts through the body-diode of HS-FET.

The boost-current limit is programmed by the ICH resistor. The programmed boost-switching current limit can be estimated with:

$$I_{CH}(A) = \frac{35}{R_{ICH}(k\Omega)} + \frac{V_{IN}}{L \times 10^7}$$

Where R_{ICH} is the resistor connected to the ICH and L is the boost inductor.

If the ICH is floating, the boost-peak current limit is about 960mA (for typical 12V input and 10uH inductor applications).

MP5512 has over-voltage protection for STRG voltage. If the feedback voltage of V_{STRG} on FBS is over 1.1 x $V_{FBS-REF}$, MP5512 shuts down the low-side MOSFET

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in both boost and buck mode until V_{STRG} drops to the regulated voltage.

Release

Once the input power drops, and DET voltage is lower than 1.06×$V_{DET-REF}$, WARN gives out a warning signal to indicate the input drop condition. Once DET drops to 0.99×$V_{DET-REF}$ the internal boost converter stops charging and works in buck-release mode. Simultaneously, the hot-swap MOSFET shuts down to prevent a negative current from VB to VIN.

In buck mode, the part transfers energy from the high-voltage storage capacitor to the low-voltage bus capacitor. The regulated bus voltage is determined by $V_{FBB-REF}$ and the resistor divider from VB to FBB.

The released buck adopts a fixed-frequency constant-on-time (COT) mode. The buck converter works until the storage-capacitor voltage approaches the bus voltage. The storage and bus voltages drop simultaneously until they reach the downstream DC-DC converter's UVLO or VB_UVLO (see Figure 3).

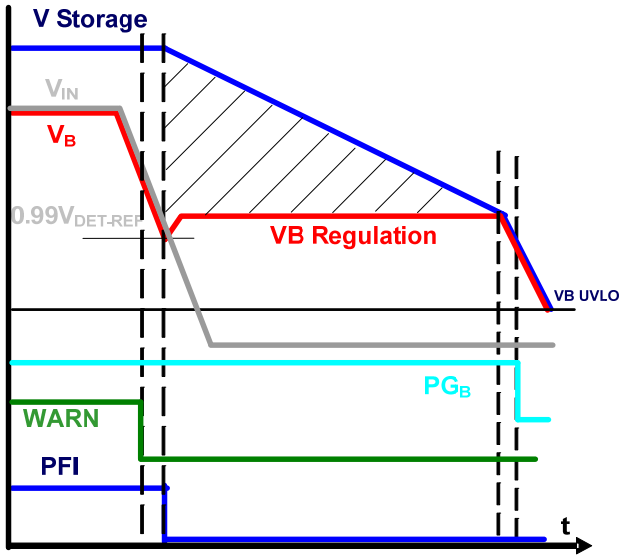


Figure 3: Release Times

The buck mode has a peak-current limit function to limit the release current; the released-peak current is about 5A. If an inductor current triggers the current limit, the high-side switch won't turn on until the inductor current drops to a valley-current limit. The buck converter works in pulse-skip mode at light load to save the switching-power loss.

Input Recovery Start-up

If the input power fails and comes back before VB drops to UVLO, the storage capacitor re-charges. In this condition, PFI switches to high, and the hot-swap MOSFET turns on (if V_{IN} is 190mV higher than VB). Following a 1.8ms delay (after DVDT saturation), the buck function turns off and boost function is re-enabled to regulate the storage capacitor at V_{STRG} voltage. See Figure 4 for the re-charge sequence. If PFI goes high but V_{IN} is still lower than VB, the hot-swap MOSFET cannot turn on. The buck regulator slightly decreases the regulated VB voltage so the hot-swap MOSFET can turn on again.

If VB drops lower than UVLO before V_{IN} returns, MP5512 begins a new startup sequence as the V_{IN} rises.

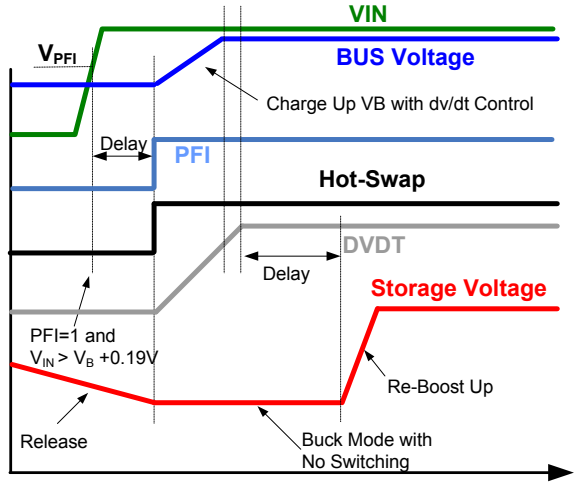


Figure 4: Re-Charge Sequence

Input-Current Limit

The input-current limit controls the inrush current of the internal hot-swap MOSFET at startup. A capacitor connected to DVDT sets the soft-start time. In addition to soft-start, the ILIM limits the steady-state current by connecting a resistor between ILIM and AGND. The current limit can be estimated from:

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$$I_{ILIM}(A) = \frac{17.2}{R_{ILIM}(k\Omega)} - 0.085$$

Where, R_{ILIM} is the current-limit setting resistor from ILIM to GND.

The voltage on ILIM monitors and indicates the current in the hot-swap MOSFET. The relationship between the input current and ILIM voltage can be estimated by:

$$V_{ILIM}(V) = \frac{I_{IN}(A) \times R_{ILIM}(k\Omega)}{14.6} + 0.0085 \times R_{ILIM}(k\Omega)$$

Reverse-Current Protection

The V_{in}-to-VB hot-swapping MOSFET turns on when input voltage exceeds the VIN UVLO threshold (during initial start up). It turns off when DET voltage falls, causing the MP5512 to enter buck-release mode. It turns on again if $V_{IN} > V_B + 0.19V$.

The hot-swapping circuit applies reverse-current protection when energy is released from the storage capacitors to VB. Typically 150mA reverse current from VB to V_{IN} shuts down the hot-swap MOSFET.

Power-On Reset Delay and VB Rising Control

TPOR controls the power-on-reset function for hot-swapping. By floating TPOR, the TPOR time is about 0.35ms. If an external capacitor is connected to TPOR, an internal 1μA current charges the capacitor and determines the TPOR time (with 0V-to-1V TPOR capacitor charge time). The power-reset-delay time can be estimated as:

$$T_D = \frac{C_{TPOR} \times 1V}{1\mu A}$$

After TPOR time, one capacitor across the DVDT programs VB soft-start time. During the SS period, the relationship between VB and DVDT voltage can be estimated by:

$$VB = 15.4 \times V_{DVDT}$$

Where, V_{DVDT} is DVDT capacitor voltage charged by 1μA current (eventually V_{DVDT} is charged saturated to about 1.23V).

The VB soft-start time from 0V to V_{IN} can be estimated by:

$$T_R = \frac{VB \times C_{DVDT}}{15.4 \times 1\mu A}$$

By floating DVDT, the VB rising time from 0V to 12V is typically 0.9ms.

Start-Up Sequencing

After the IC is enabled, MP5512 starts to work with the TPOR reset time and DVDT soft-start time. During VB rising time, an internal charge pump charges the CST capacitor. This provides the driver source for the hot-swap MOSFET. Too short of a DVDT time may trigger the input current-limit threshold. Too large of a CST capacitor may affect the charge-pump slew rate. A 10nF CST capacitor is recommended. During DVDT soft-start, the VB capacitor is charged; the STRG capacitor is not charged.

Once VB is charged, DVDT voltage charges to about 1.23V and holds at this saturated voltage. If PFI is high and DVDT saturates, the charge function is enabled and the storage capacitor charges to target voltage.

VCC Power Management

MP5512 internal circuits are powered from the Vcc capacitor, which is regulated by V_{IN} in normal conditions. In case of V_{IN} failure, a Vcc power source is supplied by the VB source allowing the buck converter to continue to work. A capacitor with no less than 1uF is required to VCC.

Enable Control

The MP5512 EN and ENCH have different functions. EN enables/disables all internal circuits, and ENCH only controls the boost-charge of the storage voltage. When ENCH is high, boost functions and storage voltage are regulated. Once ENCH is pulled low, the boost mode stops and storage voltage discharges from the leakage current. The ENCH signal cannot control buck mode. The buck converter continues to work if input power fails, even when ENCH is low. Normally, EN must be pulled up to both Vin and VB, and ENCH must be pulled up to VB or VCC.

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EN and ENCH cannot be connected to voltage higher than 6.5V. For a resistor pull-up condition, an internal zener diode clamps the voltage at EN/ENCH. The maximum pull-up current for the internal zener clamp (assuming the worst case with 6V) should be less than 0.2mA. Pulled up to Vin and VB, a typical 100k Ω pull-up resistor is recommended.

Bus Voltage Power-Good Indicator (PG_B)

When the voltage on the FBB (VB feedback) drops below $0.9\times V_{FBB-REF}$, the MP5512 internally pulls the PGB low. When the FBB voltage is above $0.95\times V_{FBB-REF}$, it goes high (if externally pulled up by a resistor).

Input-Power Warning and Power-Failure Indicator (PFI)

When the voltage on the DET (VIN feedback) rises to $1.08\times V_{DET-REF}$, WARN goes high (if externally pulled up by a resistor). It pulls low if DET voltage drops to $1.06\times V_{DET-REF}$. There is a warning signal for the next power stage by informing the VIN drop portent.

If DET drops below $0.99\times V_{DET-REF}$, the MP5512 internally pulls the PFI low. This signals the DET to leave boost mode. If DET voltage rises to $1.02xV_{DET-REF}$, PFI sets to high again (if externally pulled up by a resistor).

Residual Storage-Energy Discharge

In buck release mode, MP5512 discharges the storage voltage to VB_UVLO, but the residual voltage holds for a longer time period due to the large storage capacitance. The residual voltage is worse if MP5512 is disabled by the EN signal.

When MP5512 is disabled, RTEST is pulled to PGND internally, an external resistor from V_{STRG} to RTEST helps to discharge the residual energy. The RTEST is self-driven and storage voltage is discharged to about 0.8V, even if MP5512 input is not available. Choose an efficient, external discharge resistor to limit the maximum RTEST current to lower than 500mA.

Thermal Shut Down (TSD)

Thermal shutdown is implemented to prevent the chip from thermal damage. When the silicon die temperature is higher than its upper threshold, it shuts down the chip. When the temperature is lower than its lower threshold, the chip is enabled again with a new start-cycle.

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APPLICATION INFORMATION

Setting the Storage Voltage

Set the storage voltage by choosing the external feedback resistors R5 and R6 (see Figure 5)..

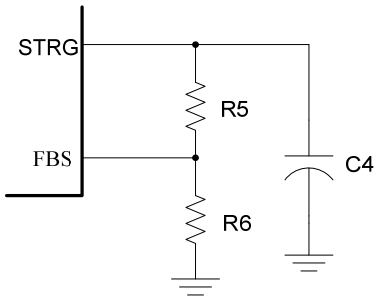


Figure 5: Storage Feedback Circuit

The storage voltage is determined by:

$$V_{STORAGE} = (1+\frac{R5}{R6}) \times V_{FBS-REF}$$

Where, $V_{FBS-REF}$ is 0.8V typically. R5 and R6 are not critical for normal operation. Select an R6 resistor higher than 10kΩ to reduce the bleed current and lower than 50kΩ to enhance noise immunity. For example, if R6 is 10kΩ, R5 is calculated as:

$$R5 = \frac{10k\Omega \times (V_{STORAGE} - V_{FBS-REF})}{V_{FBS-REF}}$$

For a 24V storage voltage, R5 is 290kΩ.

Table 1 lists the recommended feedback resistance for different storage voltages.

Table 1: Resistor Pairs for $V_{STORAGE}$

$V_{STORAGE}$(V)	R5 (kΩ)	R6 (kΩ)
12	140	10
24	290	10
40	490	10

Setting VIN Power-Failure Threshold Voltage and VB Release-Regulation Voltage

Set the release-trigger voltage by choosing the external feedback resistors R1 and R2 (see Figure 6). Release-trigger voltage is determined by 0.99x$V_{DET-REF}$, which is 0.792V.

The input power-failure release threshold is:

$$V_{PFI} = (1+\frac{R1}{R2}) \times 0.792V$$

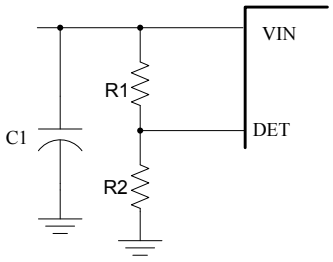


Figure 6: Release-Feedback Circuit

V_{DET} determines the release-trigger voltage and V_{FBB} determines VB release-regulation voltage (see Figure 7).

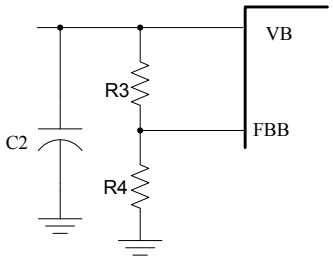


Figure 7: VB Regulation Feedback Circuit

The bus-regulation voltage can be calculated by:

$$VB_{RLS} = (1+\frac{R3}{R4}) \times (V_{FBB-REF} + \frac{V_{RAMP}}{2})$$

Where, V_{RAMP} is buck FBB internal compensation ramp voltage, and can be estimated as:

$$V_{RAMP} = V_{STRG} \times D \times (1-D) \times \frac{10^6}{220 \times F_{SW}})$$

Where, $V_{FBS-REF}$ is 0.8V typically. D is the buck duty cycle, and F_{SW} is the switching frequency.

R3 and R4 are related to buck-release stability. Since the release-buck mode works in COT mode, try to avoid small resistor values that affect the internal voltage ramp. Generally, choose R3//R4≥10kΩ for stable performance with C_B=22μF.

Selecting the Storage Capacitor

The storage capacitor stores energy during normal operation and releases this energy to VB when VIN loses input power. Use a general-

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purpose electrolytic capacitor or low-profile POS capacitor for most applications. Select a storage capacitor with a voltage margin 20% higher than the targeted storage voltage. When choosing the capacitors, consider the capacitance reduction with the DC voltage offset. Different capacitors have different capacitance de-rating performances. Choose a capacitor with a voltage rating high enough to guarantee enough capacitance.

The required capacitance depends on the length of the "dying gasp" for a typical application. Assume the bus-release current is $I_{RELEASE}$ when bus voltage is regulated at VB_{RLS} for the DC-DC converter. The storage is V_{STRG}, and the required dying gasp time is τ_{DASP}. The required storage capacitance is:

$$C_{STRG} = \frac{2 \times VB_{RLS} \times I_{RELEASE} \times \tau_{DASP}}{(V_{STRG}^2 - VB_{RLS}^2) \times Eff}$$

Eff is the energy-release efficiency in the buck converter, which can run up to 90% efficiency in most applications. Select the proper storage capacitance to ensure enough capacitance for buck-power loss. If $I_{RELEASE}$=1A, τ_{DASP}=20ms, $V_{STORAGE}$=24V, and VB_{RLS-}=10V, then the required storage capacitance is 1000μF.

Setting the Input Hot-Swap Current Limit

Connect a resistor from ILIM to AGND to set the current-limit value. For example, a 8.25kΩ resistor sets the current limit to about 2A. Refer to the "Input-Current Limit" section for current-limit calculation. Table 2 lists recommended resistors for different current-limit values.

Table 2: I_{LIM} vs. R_{ILIM}

I_{LIM}(A)	R_{LIM} (kΩ)
4.5	3.74
3.54	4.75
2	8.25

Setting the Boost Peak-Current Limit

Connect a resistor from ICH to AGND to set the boost peak-inductor current. Refer to the "Storage Voltage" section for boost-peak current-limit setting calculation. If ICH is floating, the boost peak-current limit is about 960mA (in typical 12V input and 10μH inductor conditions).

Selecting the Inductor

The inductor is necessary to supply constant current to the load. Since the boost mode and buck mode share the same inductor (and generally buck-mode current is higher), the inductor supporting the buck-mode releasing current is recommended.

Select the inductor based on the buck-releasing mode. If the storage voltage is V_{STRG}, the bus-regulation voltage is VB_{RLS}, with the buck running at a fixed 500kHz frequency. The inductance value can be calculated by:

$$L = \frac{VB_{RLS}}{\Delta I_L \times F_{SW}} \times (1 - \frac{VB_{RLS}}{V_{STRG}})$$

Where ΔI_L is the peak-to-peak inductor-ripple current, which can be set at 30% to 40% of the full-releasing current.

The inductor should not saturate under the maximum inductor-peak current.

Setting the Power-On-Reset Delay Time

Connect a capacitor to the TPOR to set the power–on-reset delay time. Leave it floating for the default delay time of around 0.35ms. Table 3 lists the recommended capacitors for different delay times.

Table 3: Reset Delay vs. Capacitor Value

τ_D (ms)	C_{TPOR} (nF)
100	100
500	500

Setting the Bus Voltage Rise Time

Connect a capacitor to the DVDT to set the bus voltage start-up slew rate and soft-start time. Leave it floating for the default soft-start time (around 0.9ms from 0V to 12V). Table 4 lists the recommended capacitors for different soft-start times for a 12V input condition. It has a proportional VB soft-start time in other input voltage conditions.

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Table 4: Soft-Start vs. Capacitor Value when V_{IN}=12V

T_R (ms)	$C_{dv/dt}$ (nF)
7.8	10
78	100

Selecting BST and CST Capacitance

The BST capacitor supplies power to the buck converter high-side MOSFET. A 0.1uF~1uF ceramic capacitor is recommended for BST decoupling. The CST capacitor supplies power for the input hot-swap MOSFET and the STRG disconnecting MOSFET. The CST capacitor also supplies power to BST when the buck is working in a 100% duty cycle. The CST capacitor is charged by an internal charge pump; a 10nF ceramic capacitor is recommended. A CST capacitor with more than 47nF capacitance is not recommended as it affects the voltage charge-up slew rate.

Selecting Input Capacitor and TVS

Capacitors at VIN are recommended to absorb possible voltage spikes during input-power turn on, input-switch hard off (during power off), or other special conditions. The application determines the capacitor. For example, if the input power trace is too long (with higher parasitic inductance), during the input-switch hard off period, more energy pumps into the input. This means more input capacitors are needed for the input voltage spike to stay in a safe range. Use a 0.1uF or larger capacitor.

Keep inrush-current requirements in mind when selecting an input capacitor. Typically, more input capacitors result in a higher input-inrush current during hot-plugging. A smaller input capacitor is needed for a smaller inrush current. MP5512 works normally with a very small input capacitor. It works without an input capacitor as well. However, this leads to a possible high-voltage spike. An efficient solution is to add a TVS diode at the input to absorb the possible input-voltage spike. At the same time, keep the inrush current small during hot-plugging. A typical TVS diode, like SMA6J13A is recommended.

Selecting the External Diode

For release-mode, one schottky diode between SW and PGND is recommended. This diode conducts a low-side current during switching dead-time or a high-switching current condition. Small package diodes such as DFLS260 or SBR3U60P1 are recommended due to their small package size, low voltage drop and high-power capabilities.

For charge mode, the internal high-side MOSFET is not turned on and current is conducted through the MOSFET body-diode. One schottky diode between SW and STRG is recommended since the boost-peak current can reach up to 2A. The diode-voltage rating should be higher than the storage voltage. The current rating should be higher than the diode current programmed by ICH. Small package diodes such as DFLS260 or SBR3U60P1 are recommended. This diode is not necessary if the boost peak-current limit is as low as 0.5A.

Layout Recommendation

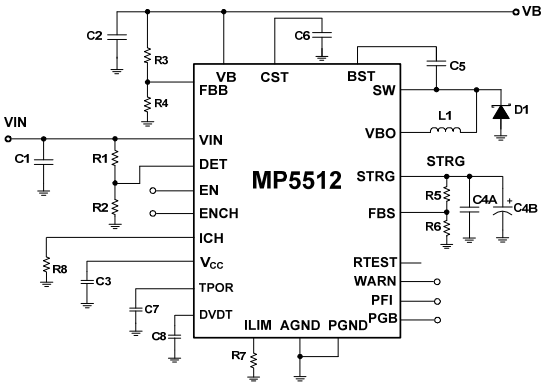
1) The high-current paths (VIN, VB, VBO, SW, STRG, and PGND) should use short, wide and direct traces.
2) While VBO is far from SW, keep the SW trace as short as possible.
3) Put the decoupling capacitor across VB and PGND (as close as possible).
4) Put the schottky diode D1 across SW and PGND as close to the IC as possible.
5) Put the decoupling capacitor across STRG and PGND (as close as possible). When using a large volume capacitor, a small size 1uF ceramic capacitor is required. Place it as close to STRG and PGND as possible.
6) Put the decoupling capacitor across Vcc and AGND (as close as possible).
7) Keep the switching node SW short and away from the feedback network.

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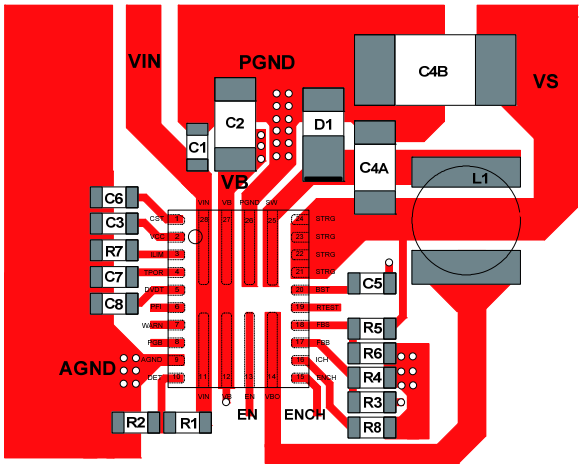
8) The external feedback resistors should be placed next to FBB/FBS/DET.

9) Keep the BST voltage path (BST, C5 and SW) as short as possible.

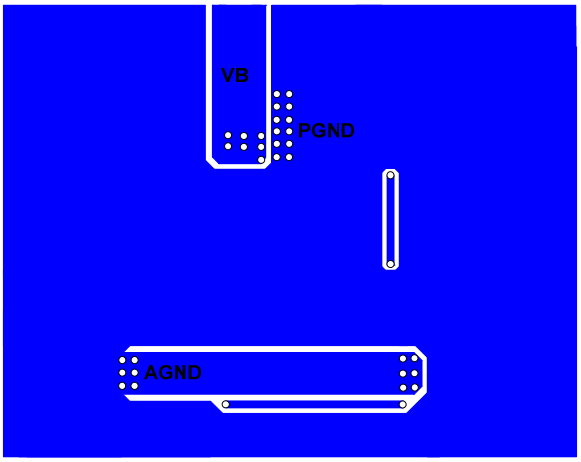
10) All signal grounds should be connected together and then connected to PGND with a one-point connection.



Schematic for Layout



Top Layer



Bottom Layer

Figure 8: Layout Recommendation

Design Example

Below is a design example following the application guidelines for the following specifications:

Table 5: Design Example

Parameter	Symbol	Value	Units
Input Voltage	V_{IN}	12	V
Storage Voltage	V_{STRG}	35	V
Input Pfail Threshold	V_{PFI}	6.1	V
Bus Backup Voltage	V_{RLS}	7.8(9)	V
Bus Backup Max Load	$I_{RELEASE}$	3	A

See Figures 9 and 10 for detailed application schematics, and the typical performance waveforms. For more detailed device applications, please refer to related evaluation board datasheets.

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TYPICAL APPLICATION CIRCUITS

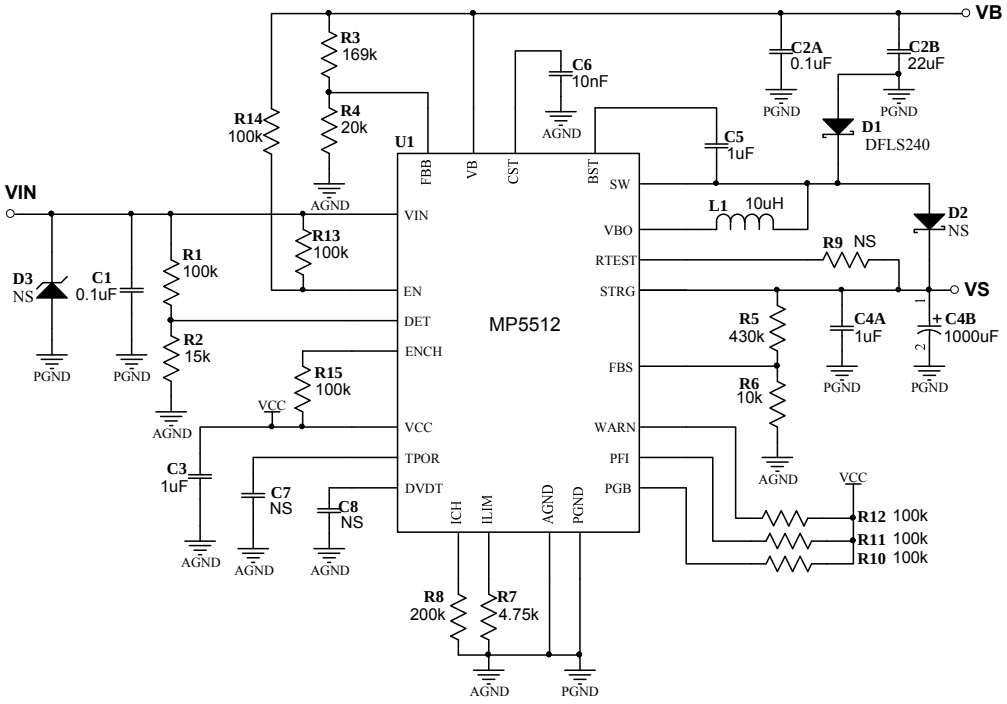


Figure 9: 12V Input, 35V Storage Typical Application Circuit

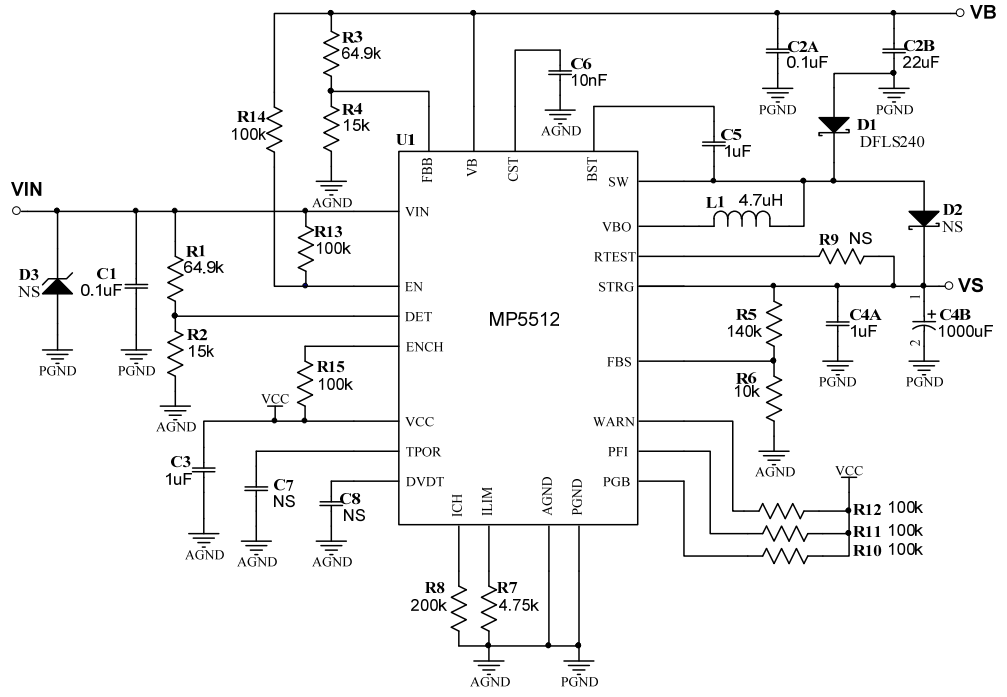
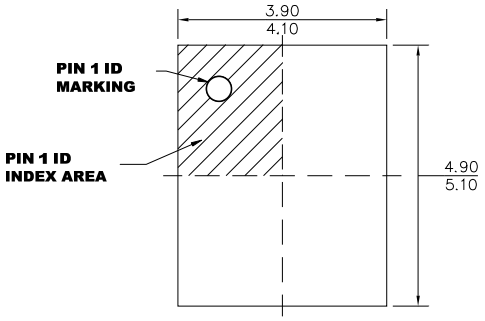


Figure 10: 5V Input, 12V Storage Typical Application Circuit

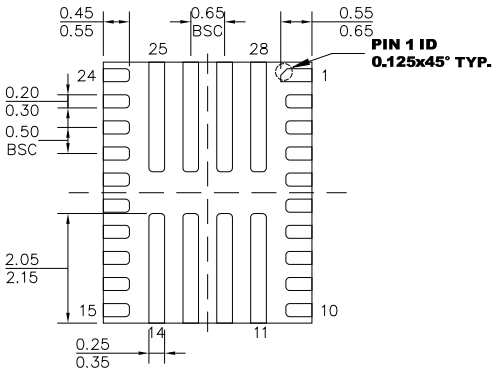
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PACKAGE INFORMATION

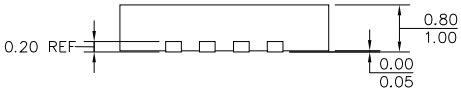
QFN-28 (4mmX5mm)



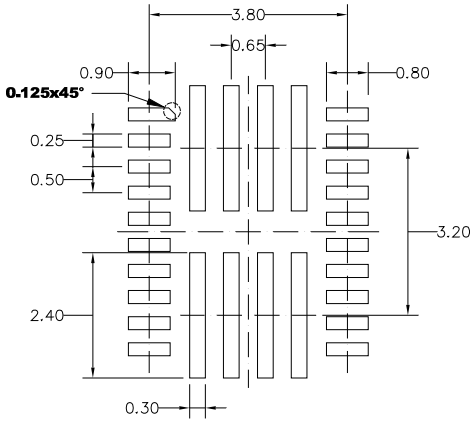
TOP VIEW



BOTTOM VIEW



SIDE VIEW



RECOMMENDED LAND PATTERN

NOTE:

1) ALL DIMENSIONS ARE IN MILLIMETERS.
2) EXPOSED PADDLE SIZE DOES NOT INCLUDE MOLD FLASH.
3) LEAD COPLANARITY SHALL BE 0.10 MILLIMETERS MAX.
4) JEDEC REFERENCE IS MO-220.
5) DRAWING IS NOT TO SCALE.

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